

# 2-Mbit (256 K × 8) Static RAM

### **Features**

- Pin and function compatible with CY7C1010CV33
- High speed

  □ t<sub>AA</sub> = 10 ns
- Low active power
  □ I<sub>CC</sub> = 90 mA at 10 ns
- Low CMOS standby power
  □ I<sub>SB2</sub> = 10 mA
- 2.0 V data retention
- Automatic power down when deselected
- TTL-compatible inputs and outputs
- Easy memory expansion with CE and OE features
- Available in Pb-free 36-pin SOJ and 44-pin TSOP II packages

### **Functional Description**

The CY7C1010DV33 is a high performance CMOS Static RAM organized as 256 K words by 8 bits. Easy memory expansion is provided by an active LOW Chip Enable ( $\overline{\text{CE}}$ ), an active LOW Output Enable ( $\overline{\text{OE}}$ ), and three-state drivers. Writing to the device is accomplished by taking Chip Enable ( $\overline{\text{CE}}$ ) and Write Enable ( $\overline{\text{WE}}$ ) inputs LOW. Data on the eight I/O pins (I/O<sub>0</sub> through I/O<sub>7</sub>) is then written into the location specified on the address pins (A<sub>0</sub> through A<sub>17</sub>).

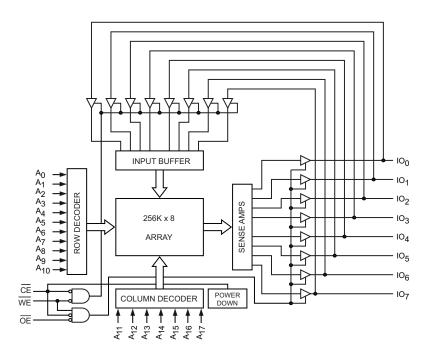
Reading from the device is accomplished by taking Chip Enable (CE) and Output Enable (OE) LOW while forcing Write Enable (WE) HIGH. Under these conditions, the contents of the memory location specified by the address pins will appear on the I/O pins.

The eight input and output pins (I/O $_0$  through I/O $_7$ ) are placed in a high impedance state when the device is deselected ( $\overline{\text{CE}}$  HIGH), the outputs are disabled ( $\overline{\text{OE}}$  HIGH), or during a Write operation ( $\overline{\text{CE}}$  LOW, and  $\overline{\text{WE}}$  LOW).

The CY7C1010DV33 is available in 36-pin SOJ and 44-pin TSOP II packages with center power and ground (revolutionary) pinout.

For a complete list of related documentation, click here.

## **Logic Block Diagram**





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### **Selection Guide**

Description	-10	Unit
Maximum Access Time	10	ns
Maximum Operating Current	90	mA
Maximum CMOS Standby Current	10	mA

### **Pin Configuration**

Figure 1. 36-pin SOJ pinout [1]

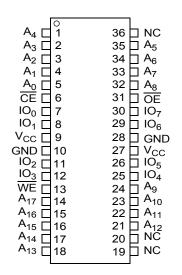
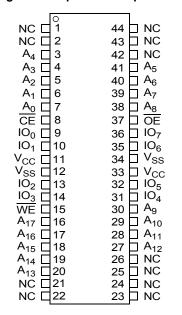


Figure 2. 44-pin TSOP II pinout [1]



### Note

NC pins are not connected on the die.



## **Maximum Ratings**

Exceeding the maximum ratings may impair the useful life of the device. These user guidelines are not tested.

Storage Temperature ......-65 °C to +150 °C Ambient Temperature with Power Applied .......55 °C to +125 °C

Supply Voltage on V  $_{CC}$  Relative to GND  $^{[2]}$  .....–0.5 V to +4.6 V

DC Input Voltage [2]	0.3 V to V <sub>CC</sub> + 0.3 V
Current into Outputs (LOW)	20 mA
Static Discharge Voltage (MIL-STD-883, Method 3015)	> 2001 V
Latch Up Current	> 200 mA

## **Operating Range**

Range	Ambient Temperature	V <sub>CC</sub>
Industrial	–40 °C to +85 °C	$3.3 \text{V} \pm 0.3 \text{V}$

### **Electrical Characteristics**

Over the Operating Range

Dawawataw	Decemention	Took Conditions		-	10	
Parameter	Description	Test Conditions			Max	Unit
V <sub>OH</sub>	Output HIGH Voltage	V <sub>CC</sub> = Min; I <sub>OH</sub> = -4.0 mA		2.4	_	V
V <sub>OL</sub>	Output LOW Voltage	V <sub>CC</sub> = Min; I <sub>OL</sub> = 8.0 mA		-	0.4	V
V <sub>IH</sub>	Input HIGH Voltage			2.0	V <sub>CC</sub> + 0.3	V
V <sub>IL</sub>	Input LOW Voltage <sup>[2]</sup>			-0.3	0.8	V
I <sub>IX</sub>	Input Leakage Current	$GND \le V_1 \le V_{CC}$		<b>–</b> 1	+1	μΑ
I <sub>OZ</sub>	Output Leakage Current	GND ≤ V <sub>OUT</sub> ≤ V <sub>CC</sub> , Output Disabled		<b>–</b> 1	+1	μΑ
I <sub>CC</sub>	V <sub>CC</sub> Operating Supply Current	$V_{CC}$ = Max, f = $f_{MAX}$ = $1/t_{RC}$	100 MHz	_	90	mA
			83 MHz	_	80	
			66 MHz	-	70	
			40 MHz	-	60	
I <sub>SB1</sub>	Automatic CE Power-down Current – TTL Inputs	$\begin{array}{l} \text{Max V}_{CC}, \overline{CE} \geq \text{V}_{IH}; \text{V}_{IN} \geq \text{V}_{IH} \text{ or} \\ \text{V}_{IN} \leq \text{V}_{IL}, \text{f} = \text{f}_{MAX} \end{array}$		_	20	mA
I <sub>SB2</sub>	Automatic CE Power-down Current – CMOS Inputs	$\begin{array}{c} \text{Max V}_{CC}, \ \overline{\text{CE}} \geq \text{V}_{CC} - 0.3 \text{ V}, \\ \text{V}_{\text{IN}} \geq \text{V}_{CC} - 0.3 \text{ V}, \text{ or V}_{\text{IN}} \leq 0.3 \text{ V}, \text{ f} = 0.0 \text{ V}, \\ \text{Max V}_{\text{CC}} = 0.3 \text{ V}, \text{ or V}_{\text{IN}} \leq 0.3 \text{ V}, \text{ f} = 0.0 \text{ V}, \\ \text{Max V}_{\text{CC}} = 0.3 \text{ V}, \text{ or V}_{\text{IN}} \leq 0.3 \text{ V}, \text{ f} = 0.0 \text{ V}, \\ \text{Max V}_{\text{CC}} = 0.3 \text{ V}, \text{ or V}_{\text{IN}} \leq 0.3 \text{ V}, \text{ f} = 0.0 \text{ V}, \\ \text{Max V}_{\text{CC}} = 0.3 \text{ V}, \text{ or V}_{\text{IN}} \leq 0.3 \text{ V}, \text{ f} = 0.0 \text{ V}, \\ \text{Max V}_{\text{CC}} = 0.3 \text{ V}, \text{ or V}_{\text{IN}} \leq 0.3 \text{ V}, \\ \text{Max V}_{\text{CC}} = 0.3 \text{ V}, \text{ or V}_{\text{IN}} \leq 0.3 \text{ V}, \\ \text{Max V}_{\text{CC}} = 0.3 \text{ V}, \\ \text{Max V}_$	0	_	10	mA

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<sup>2.</sup>  $V_{IL}$  (min.) = -2.0V and  $V_{IH}$  (max.) =  $V_{CC}$  + 2.0V for pulse durations of less than 20 ns.



## Capacitance

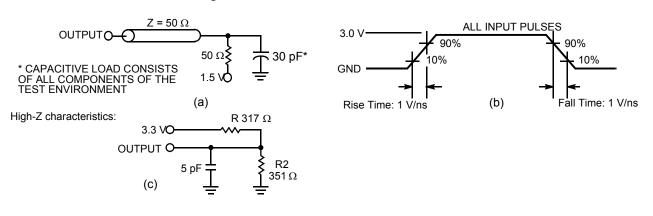
Parameter [3]	Description	Test Conditions	36-pin SOJ	44-pin TSOP II	Unit
C <sub>IN</sub>	Input capacitance	$T_A = 25 ^{\circ}\text{C}, f = 1 \text{MHz}, V_{CC} = 3.3 \text{V}$	8	8	pF
C <sub>OUT</sub>	I/O capacitance		8	8	pF

### **Thermal Resistance**

Parameter [3]	Description	Test Conditions	36-pin SOJ	44-pin TSOP II	Unit
$\Theta_{JA}$		Still air, soldered on a 3 × 4.5 inch, four layer printed circuit board	59.17	50.66	°C/W
$\Theta_{\sf JC}$	Thermal resistance (junction to case)		32.63	17.77	°C/W

### **AC Test Loads and Waveforms**

Figure 3. AC Test Loads and Waveforms [4]



Tested initially and after any design or process changes that may affect these parameters.

AC characteristics (except High Z) are tested using the load conditions shown in Figure 3 (a). High-Z characteristics are tested for all speeds using the test load shown in Figure 3 (c).



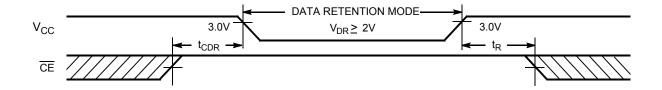
### **Data Retention Characteristics**

Over the Operating Range

Parameter [5]	Description	Conditions	Min	Max	Unit
$V_{DR}$	V <sub>CC</sub> for Data Retention		2	_	V
I <sub>CCDR</sub>	Data Retention Current	$V_{CC} = V_{DR} = 2.0 \text{ V}, \overline{CE} \ge V_{CC} - 0.3 \text{ V},$ $V_{IN} \ge V_{CC} - 0.3 \text{ V or } V_{IN} \le 0.3 \text{ V}$	-	10	mA
t <sub>CDR</sub> <sup>[6]</sup>	Chip Deselect to Data Retention Time		0	_	ns
t <sub>R</sub> <sup>[7]</sup>	Operation Recovery Time		t <sub>RC</sub>	-	ns

### **Data Retention Waveform**

Figure 4. Data Retention Waveform



### Notes

- No inputs may exceed V<sub>CC</sub> + 0.3 V.
   Tested initially and after any design or process changes that may affect these parameters.
   Full device operation requires linear V<sub>CC</sub> ramp from V<sub>DR</sub> to V<sub>CC(min.)</sub> ≥ 50 μs or stable at V<sub>CC(min.)</sub> ≥ 50 μs.



## **AC Switching Characteristics**

Over the Operating Range

Parameter [8]	Description		10	
Parameter [9]	Description	Min	Max	Unit
Read Cycle			•	
t <sub>power</sub> <sup>[9]</sup>	V <sub>CC</sub> (typical) to the first access	100	_	μS
t <sub>RC</sub>	Read Cycle Time	10	_	ns
t <sub>AA</sub>	Address to Data Valid	_	10	ns
t <sub>OHA</sub>	Data Hold from Address Change	3	_	ns
t <sub>ACE</sub>	CE LOW to Data Valid	-	10	ns
t <sub>DOE</sub>	OE LOW to Data Valid	-	5	ns
t <sub>LZOE</sub>	OE LOW to Low Z [10]	0	_	ns
t <sub>HZOE</sub>	OE HIGH to High Z <sup>[10, 11]</sup>	-	5	ns
t <sub>LZCE</sub>	CE LOW to Low Z <sup>[10]</sup>	3	_	ns
t <sub>HZCE</sub>	CE HIGH to High Z <sup>[10, 11]</sup>	_	5	ns
t <sub>PU</sub>	CE LOW to Power-up	0	_	ns
t <sub>PD</sub>	CE HIGH to Power-down	-	10	ns
Write Cycle <sup>[12,</sup>	13]	·		
t <sub>WC</sub>	Write Cycle Time	10	_	ns
t <sub>SCE</sub>	CE LOW to Write End	7	_	ns
t <sub>AW</sub>	Address Set-up to Write End	7	_	ns
t <sub>HA</sub>	Address Hold from Write End	0	_	ns
t <sub>SA</sub>	Address Set-up to Write Start	0	_	ns
t <sub>PWE</sub>	WE Pulse Width	7	_	ns
t <sub>SD</sub>	Data Set-up to Write End	5	_	ns
t <sub>HD</sub>	Data Hold from Write End	0	_	ns
t <sub>LZWE</sub>	WE HIGH to Low Z <sup>[10]</sup>	3	_	ns
t <sub>HZWE</sub>	WE LOW to High Z <sup>[10, 11]</sup>	_	5	ns

### Notes

<sup>8.</sup> Test conditions assume signal transition time of 3 ns or less, timing reference levels of 1.5 V, input pulse levels of 0 to 3.0 V.

 <sup>1</sup>est conditions assume signal transition time of 3 ns or less, timing reference levels of 1.5 V, input pulse levels of 0 to 3.0 V.
 1. the power gives the minimum amount of time that the power supply should be at stable, typical V<sub>CC</sub> values until the first memory access can be performed.
 10. At any given temperature and voltage condition, the power supply should be at stable, typical V<sub>CC</sub> values until the first memory access can be performed.
 11. the power that the power supply should be at stable, typical V<sub>CC</sub> and the power supply should be at stable, typical V<sub>CC</sub> and the power supply should be at stable, typical V<sub>CC</sub> and the power supply should be at stable, typical V<sub>CC</sub> and the power supply should be performed.
 12. The internal Write time of the memory is defined by the overlap of CE LOW, and WE LOW. CE and WE must be LOW to initiate a Write, and the transition of either of these signals can terminate the Write. The input data set-up and hold timing should be referenced to the leading edge of the signal that terminates the Write.
 13. The minimum Write cycle time for Write Cycle No. 3 (WE controlled, OE LOW) is the sum of the transition of the terminates the Write.



## **Switching Waveforms**

Figure 5. Read Cycle No. 1 [14, 15]

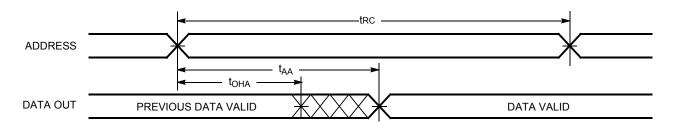
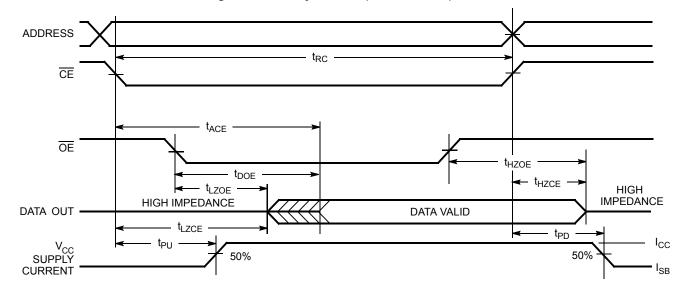


Figure 6. Read Cycle No. 2 (OE Controlled) [15, 16]



Notes
14. The device is continuously selected. OE, CE = V<sub>IL</sub>.
15. WE is HIGH for read cycle.
16. Address valid before or similar to CE transition LOW.



## Switching Waveforms (continued)

Figure 7. Write Cycle No. 1 (WE Controlled, OE HIGH During Write) [17, 18]

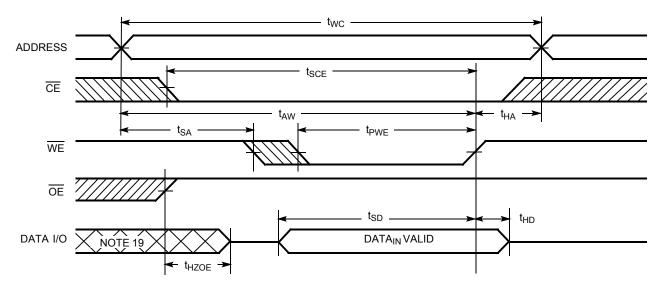
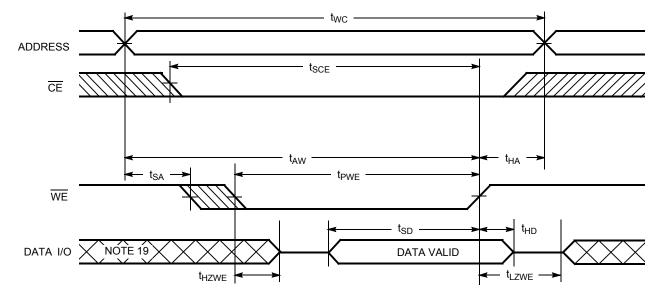


Figure 8. Write Cycle No. 2 (WE Controlled, OE LOW) [18]



<sup>17.</sup> Data IO is high impedance if  $\overline{OE} = \underline{V_{IH}}$ .

18. If  $\overline{CE}$  goes HIGH simultaneously with  $\overline{WE}$  going HIGH, the output remains in a high impedance state.

<sup>19.</sup> During this period, the I/Os are in output state and input signals should not be applied.



## **Truth Table**

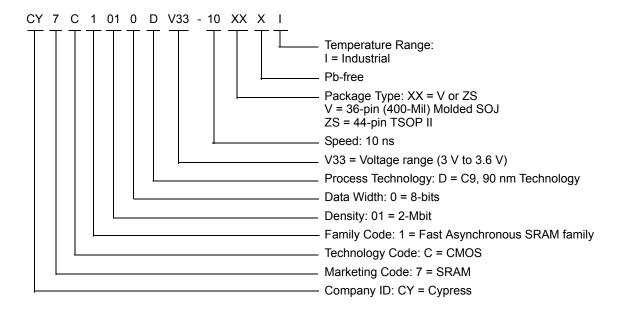
CE	OE	WE	I/O <sub>0</sub> –I/O <sub>7</sub>	I/O <sub>8</sub> –I/O <sub>15</sub>	Mode	Power
Н	Х	Х	High Z	High Z	Power Down	Standby (I <sub>SB</sub> )
L	L	Н	Data Out	Data Out	Read All Bits	Active (I <sub>CC</sub> )
L	Х	L	Data In	Data In	Write All Bits	Active (I <sub>CC</sub> )
L	Н	Н	High Z	High Z	Selected, Outputs Disabled	Active (I <sub>CC</sub> )



## **Ordering Information**

Speed (ns)	Ordering Code	Package Diagram Package Type		Operating Range
10	CY7C1010DV33-10VXI 51-85090 36-pin (400		36-pin (400-Mil) Molded SOJ (Pb-free)	Industrial
	CY7C1010DV33-10ZSXI	51-85087	44-pin TSOP II (Pb-free)	

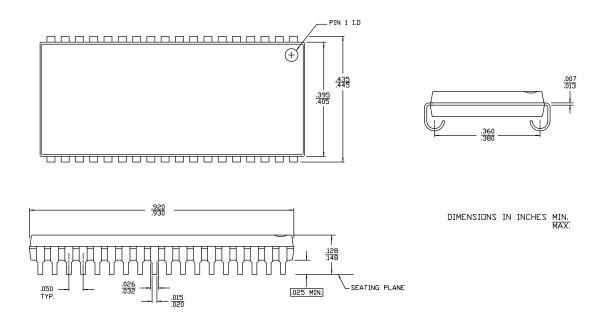
### **Ordering Code Definitions**





## **Package Diagrams**

Figure 9. 36-pin SOJ V36.4 (Molded) Package Outline, 51-85090

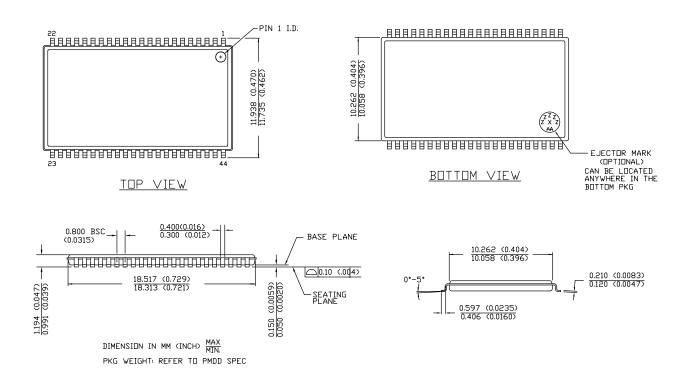


51-85090 \*F



### Package Diagrams (continued)

Figure 10. 44-pin TSOP Z44-II Package Outline, 51-85087



51-85087 \*E



## Acronyms

Acronym	Description		
CE	Chip Enable		
CMOS	Complementary Metal Oxide Semiconductor		
I/O	Input/Output		
ŌĒ	Output Enable		
SOJ	Small Outline J-lead		
SRAM	Static Random Access Memory		
TSOP	Thin Small Outline Package		
TTL	Transistor-Transistor Logic		
WE	Write Enable		

## **Document Conventions**

### **Units of Measure**

Symbol	Unit of Measure			
°C	degree Celsius			
MHz	megahertz			
μΑ	microampere			
μS	microsecond			
mA	milliampere			
mm	millimeter			
mW	milliwatt			
ns	nanosecond			
Ω	ohm			
%	percent			
pF	picofarad			
V	volt			
W	watt			



## **Document History Page**

	I	I		
Rev.	ECN No.	Submission Date	Orig. of Change	Description of Change
**	342195	See ECN	PCI	New data sheet.
*A	459073	See ECN	NXR	Converted Preliminary to Final. Removed Commercial Operating Range from product offering. Removed -8 ns and -12 speed bin Removed the Pin definitions table. Modified Maximum Ratings for DC input voltage from -0.5V to -0.3V and V <sub>CC</sub> + 0.5V to V <sub>CC</sub> + 0.3V Changed I <sub>CC</sub> max from 65 mA to 90 mA Changed the description of I <sub>IX</sub> from "Input Load Current" to "Input Leakage Current" Updated the Thermal Resistance table. Updated footnote #7 on High-Z parameter measurement Added footnote #12 Updated the Ordering Information and replaced Package Name column with Package Diagram in the Ordering Information table.
*B	2602853	11/07/08	VKN / PYRS	Added 36-pin SOJ package and its related information
*C	3059211	10/14/2010	PRAS	Added Ordering Code Definitions. Updated Package Diagrams.
*D	3272897	06/07/2011	AJU	Updated Functional Description (Removed "Refer to the Cypress application note AN1064, SRAM System Guidelines for best practice recommendations.") Added Acronyms and Units of Measure. Updated in new template.
*E	4207615	12/02/2013	MEMJ	Updated Package Diagrams: spec 51-85090 – Changed revision from *E to *F. spec 51-85087 – Changed revision from *C to *E. Updated in new template. Completing Sunset Review.
*F	4574311	11/19/2014	MEMJ	Added related documentation hyperlink in page 1.



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